



浙江世菱半导体有限公司  
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

## 产品规格书

### Specification of Products

产品名称：快恢复二极管

产品型号：MURP200400CI

浙江世菱半导体有限公司  
ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

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林益龙	曹剑龙	宗瑞

## Ultra-Fast Soft Recovery Diode Module

### Description

Ultra-FRD module devices are optimized to reduce losses and EMI/RFI in high frequency power conditioning electrical systems. These diode modules are ideally suited for power converters, motor drives and other applications where switching losses are significant portion of the total losses.

### Features

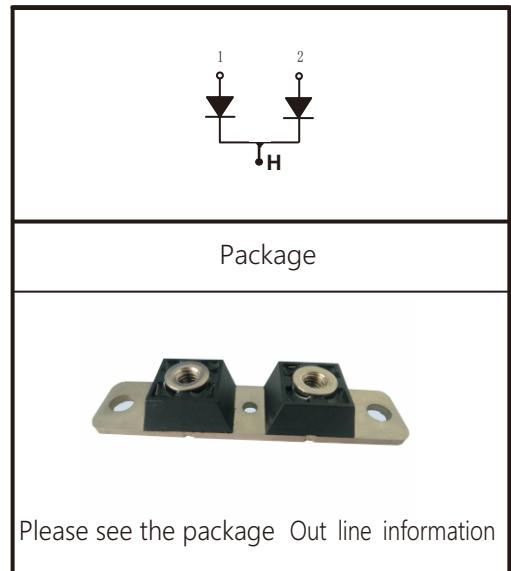
- ☛ Repetitive Reverse Voltage:  $V_{RRM} = 400V$
- ☛ Low Forward Voltage Drop :  $V_F$  (typ.) = 1.4V
- ☛ Average Forward Current :  $I_F$  (AV.) = 200A @  $T_c = 100^\circ C$
- ☛ Ultra-Fast Reverse Recovery Time :  $t_{rr}$ (typ.) = 70 ns
- ☛ Extensive Characterization of Recovery Parameters
- ☛ Reduced EMI and RFI
- ☛ Non Isolation Type Package

### Applications

Motor Drives, Free wheel use, High Power Converters, Welders, Various Switching and Telecommunication Power Supply.

### Equivalent Circuit and Package

#### Equivalent Circuit



Please see the package Out line information

### Absolute Maximum Ratings @ $T_j = 25^\circ C$ (Per Leg)

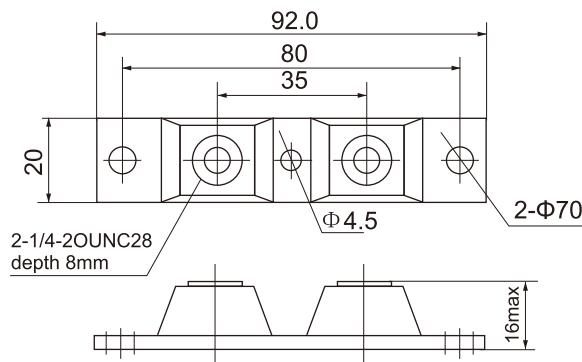
Symbol	Parameter	Conditions	Ratings	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage		400	V
$V_{R(DC)}$	Reverse DC Voltage		320	V
$I_F$ (AV)	Average Forward Current @ $T_c = 25^\circ C$ @ $T_c = 100^\circ C$	Resistive Load	400 200	A A
$I_{FSM}$	Surge (non-repetitive) Forward Current	One Half Cycle at 60Hz, Peak Value	3300	A
$I_t^2$	$I^2t$ for Fusing	Value for One Cycle Current, $t_w = 8.3ms$ , $T_j = 25^\circ C$ Start	$45.0 * 10^3$	$A^2 s$
$T_j$	Junction Temperature		-40 ~ 125	$^\circ C$
$T_{sta}$	Storage Temperature		-40 ~ 125	$^\circ C$
$P_d$	Maximum Power Dissipation		700	W
-	Mounting Torque		4.0	N. m
-	Terminal Torque		3.0	N. m

## Thermal Characteristics

Symbol	Parameter	Conditions	Values			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)}$	Thermal Resistance	Junction to Case	-	-	0.15	°C/W

## Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Conditions	Values			Unit
			Min.	Typ.	Max.	
$V_R$	Cathode Anode Breakdown Voltage	$I_R = 100\mu\text{A}$	400	-	-	V
$V_{FM}$	Maximum Forward Voltage	$I_{FM} = 300\text{A}, T_c = 25^\circ\text{C}$	-	1.4	1.5	V
$I_{RRM}$	Repetitive Peak Reverse Current	$T_c = 100^\circ\text{C}, V_{RRM}$ applied	-	-	8.5	mA
$T_{rr}$	Reverse Recovery Time	$I_{FM} = 200\text{A}, V_R = 300\text{V}$ $\frac{dI}{dt} = -100\text{A/us}$	$T_c = 25^\circ\text{C}$	-	70	ns
			$T_c = 100^\circ\text{C}$	-	100	ns



## Rating and Characteristic

### Performance Curves

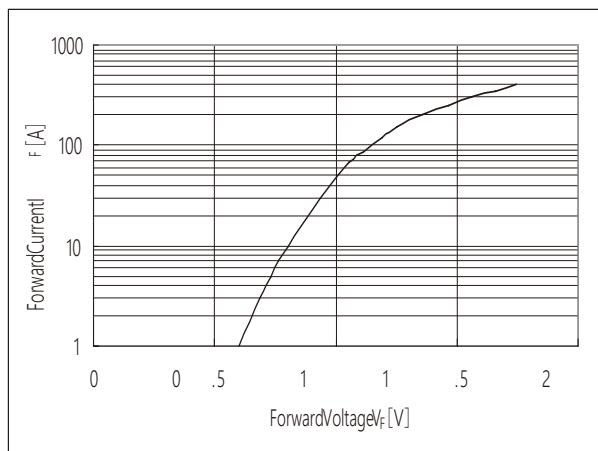


Fig. 1 : Typical Forward Voltage Drop  
vs. Instantaneous Forward Current

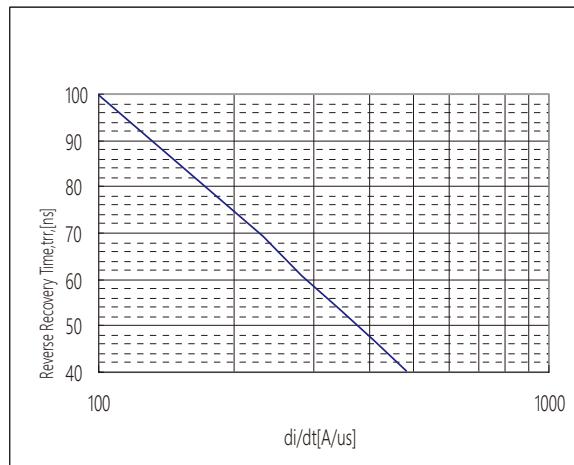


Fig. 2 : Typical Reverse Recovery Time  
vs.  $-di/dt$

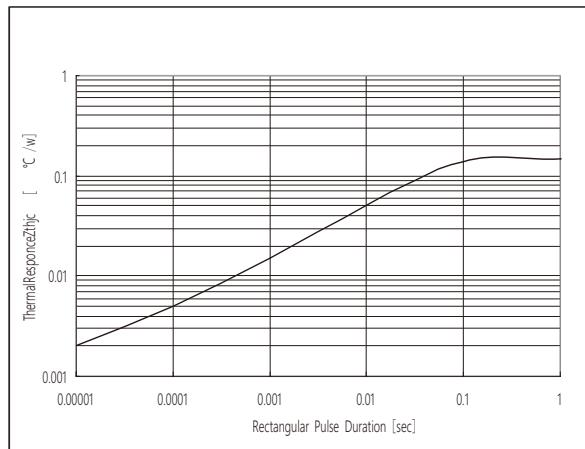


Fig. 3 : Transient Thermal Impedance( $Z_{thjc}$ )  
Characteristics

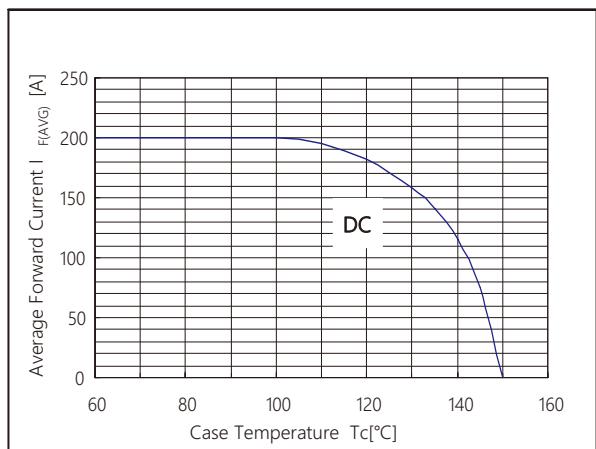


Fig. 4 : Forward Current DeratingCurve